

# Narihito Okada

## List of Publications by Year in descending order

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52  
papers

679  
citations

686830

13  
h-index

580395

25  
g-index

52  
all docs

52  
docs citations

52  
times ranked

658  
citing authors

#	ARTICLE	IF	CITATIONS
1	Epitaxial lateral overgrowth of AlN on trench-patterned AlN layers. Journal of Crystal Growth, 2007, 298, 257-260.	0.7	104
2	Dislocations in AlN Epilayers Grown on Sapphire Substrate by High-Temperature Metal-Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 1458-1462.	0.8	90
3	Impact of high-temperature growth by metal-organic vapor phase epitaxy on microstructure of AlN on 6H-SiC substrates. Journal of Crystal Growth, 2008, 310, 2308-2313.	0.7	65
4	High-efficiency AlGaN-based UV light-emitting diode on laterally overgrown AlN. Journal of Crystal Growth, 2008, 310, 2326-2329.	0.7	54
5	Controlling potential barrier height by changing V-shaped pit size and the effect on optical and electrical properties for InGaN/GaN based light-emitting diodes. Journal of Applied Physics, 2015, 117, .	1.1	40
6	Thermodynamic Aspects of Growth of AlGaN by High-Temperature Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2006, 45, 2502-2504.	0.8	26
7	Green light-emitting diodes fabricated on semipolar (11 $\bar{2}$ ) GaN on $c$ -plane patterned sapphire substrate. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 469-472.	0.8	21
8	Bulk GaN substrate with overall dislocation density on the order of 10 <sup>5</sup> /cm <sup>2</sup> fabricated by hydride vapor phase epitaxy. Journal of Crystal Growth, 2017, 478, 123-128.	0.7	21
9	Growth of N $\bar{c}$ -Polar Aluminum Nitride on Vicinal Sapphire Substrates and Aluminum Nitride Bulk Substrates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900588.	0.7	17
10	Origin of lattice bowing of freestanding GaN substrates grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2016, 119, .	1.1	16
11	Light-emitting diodes fabricated on nanopatterned sapphire substrates by thermal lithography. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2165-2167.	0.8	15
12	Growth of semipolar {10 $\bar{1}$ } GaN from $c$ -plane-like sapphire sidewall of patterned $n$ -plane sapphire substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2101-2103.	0.8	15
13	Separation of effects of InGaN/GaN superlattice on performance of light-emitting diodes using mid-temperature-grown GaN layer. Japanese Journal of Applied Physics, 2018, 57, 062101.	0.8	13
14	Potential Barrier Formed Around Dislocations in InGaN Quantum Well Structures by Spot Cathodoluminescence Measurements. Physica Status Solidi (B): Basic Research, 2018, 255, 1700358.	0.7	13
15	Correlation between structural properties and nonradiative recombination behaviors of threading dislocations in freestanding GaN substrates grown by hydride vapor phase epitaxy. CrystEngComm, 2020, 22, 8299-8312.	1.3	13
16	Growth and Characterization of Nitrogen $\bar{c}$ -Polar AlGaN/AlN Heterostructure for High $\bar{c}$ -Electron $\bar{c}$ -Mobility Transistor. Physica Status Solidi (B): Basic Research, 2020, 257, 1900589.	0.7	13
17	Growth of $m$ -Ga $\bar{c}$ N layers by epitaxial lateral overgrowth from sapphire sidewalls. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1164-1167.	0.8	12
18	Impact of thermal treatment on the growth of semipolar AlN on $m$ -plane sapphire. AIP Advances, 2018, 8, .	0.6	12

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19	Observation of dislocations and their arrays in physical vapor transport-grown AlN single-crystal substrate by synchrotron X-ray topography. Japanese Journal of Applied Physics, 2019, 58, SCCB29.	0.8	10
20	Growth of {11 $\bar{2}2$ } GaN on shallowly etched <i>c</i> -plane patterned sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 568-571.	0.8	8
21	Direct observation of inclined a-type threading dislocation with a-type screw dislocation in GaN. Journal of Applied Physics, 2017, 121, 185101.	1.1	7
22	Nanoscope spectroscopy of potential barriers formed around V-pits in InGaN/GaN multiple quantum wells on moderate temperature GaN pit expansion layers. Journal of Applied Physics, 2018, 124, .	1.1	7
23	Behavior of misfit dislocations in semipolar InGaN/GaN grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 488-491.	0.8	6
24	Fabrication of freestanding {20 $\bar{2}$ 1} GaN substrates by HVPE using SiO <sub>2</sub> masked GaN templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 401-404.	0.8	6
25	Crystalline property analysis of semipolar (20 $\bar{2}$ 1) GaN on (22 $\bar{4}3$ ) patterned sapphire substrate by X $\bar{c}$ ray microdiffraction and transmission electron microscopy. Physica Status Solidi (B): Basic Research, 2015, 252, 1149-1154.	0.7	6
26	Visualization of dislocation behavior in HVPE-grown GaN using facet controlling techniques. Physica Status Solidi (B): Basic Research, 2017, 254, 1600716.	0.7	6
27	Growth of GaN and improvement of lattice curvature using symmetric hexagonal SiO <sub>2</sub> patterns in HVPE growth. Japanese Journal of Applied Physics, 2019, 58, SC1049.	0.8	6
28	Investigation of off-cut angle of sapphire for epitaxial lateral overgrowth of AlN and fabrication of high-quality AlN template. Journal of Crystal Growth, 2022, 588, 126640.	0.7	6
29	Characterization of semipolar (11 $\bar{2}$ 2) GaN on <i>c</i> -plane sapphire sidewall of patterned <i>r</i> -plane sapphire substrate without SiO <sub>2</sub> mask. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2059-2062.	0.8	5
30	Thickness and growth condition dependence of crystallinity in semipolar (20 $\bar{2}$ 1) GaN films grown on (22 $\bar{4}3$ ) patterned sapphire substrates. Physica Status Solidi (B): Basic Research, 2015, 252, 1142-1148.	0.7	5
31	Effect of superlattice on light output power of InGaN-based light-emitting diodes fabricated on underlying GaN substrates with different dislocation densities. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 270-273.	0.8	5
32	Evaluation of multiple-quantum-well structure on InGaN template using (11 $\bar{2}$ 2) facet growth and mass transport. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2063-2065.	0.8	4
33	V-shaped pits in HVPE-grown GaN associated with columnar inversion domains originating from foreign particles of $\gamma$ -Si <sub>3</sub> N <sub>4</sub> and graphitic carbon. Micron, 2017, 94, 9-14.	1.1	4
34	Mechanism for the formation of nitrogen-filled voids after annealing of GaN on a sapphire substrate. Journal of Applied Physics, 2018, 124, .	1.1	4
35	Study of dislocations in AlN single-crystal using bright-field synchrotron x-ray topography under a multiple-beam diffraction condition. Applied Physics Letters, 2020, 117, 092102.	1.5	4
36	Deep ultraviolet emission from multiple quantum wells on flat N-polar AlN templates fabricated using periodical pulsed H <sub>2</sub> etching. Japanese Journal of Applied Physics, 2021, 60, 125502.	0.8	4

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37	Alternately double-sided growth of low-curvature GaN templates on sapphire substrates using hydride vapor phase epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 819-823.	0.7	3
38	Spatially Resolved Spectroscopy of Blue and Green InGaN Quantum Wells by Scanning Near-Field Optical Microscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700322.	0.7	3
39	Growth mechanism of nonpolar m-plane GaN on maskless patterned a-plane sapphire substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 2066-2068.	0.8	2
40	Characterization of semipolar {11 $\bar{2}$ } light-emitting diodes using a hole blocking layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 775-777.	0.8	2
41	Anisotropic radius of curvature of crystal planes in wide-bandgap semiconductor wafers measured by X-ray diffraction. <i>Japanese Journal of Applied Physics</i> , 2021, 60, 128004.	0.8	2
42	Three-dimensional curving of crystal planes in wide bandgap semiconductor wafers visualized using a laboratory X-ray diffractometer. <i>Journal of Crystal Growth</i> , 2022, 583, 126558.	0.7	2
43	Growth of semipolar {20 $\bar{2}$ } GaN and {20 $\bar{2}$ } GaN for GaN substrate. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 36-45.	0.7	1
44	Effect of InGaN/GaN Superlattice on Lattice Curvature of GaN Layers Grown on Sapphire Substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900586.	0.7	1
45	Epitaxial lateral overgrowth of thick semipolar {11 $\bar{2}$ } GaN by hydride vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 549-552.	0.8	0
46	High-quality GaN crystals grown from double-polarity hydride vapor phase epitaxy and single-polarization regrowth. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC1019.	0.8	0
47	Effect of off-angle of stripe patterns on facet stability and embedding in selective-area hydride vapor phase epitaxy growth. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC1001.	0.8	0
48	Study on higher-energy emission observed locally around V-pits on InGaN/GaN quantum wells grown on moderate-temperature GaN. <i>Journal of Applied Physics</i> , 2021, 130, 053103.	1.1	0
49	I-1-3 Etching of nano-patterned sapphire substrates using chf <sub>3</sub> and BCl <sub>3</sub> inductively coupled plasmas. <i>The Proceedings of the Conference on Information Intelligence and Precision Equipment IIP</i> , 2013, 2013, 8-12.	0.0	0
50	S1660104 Optimal design of the patterned sapphire substrate from viewpoints of light extraction efficiency and crystalline quality of light emitting diodes. <i>The Proceedings of Mechanical Engineering Congress Japan</i> , 2014, 2014, _S1660104-_S1660104-.	0.0	0
51	WeC-2-1 Transmission electron microscopy study on origin of threading dislocations in GaN layer grown on patterned sapphire substrate. <i>Proceedings of JSME-IIP/ASME-ISPS Joint Conference on Micromechatronics for Information and Precision Equipment IIP/ISPS Joint MIPE</i> , 2015, 2015, WeC-2-1-1- WeC-2-1-3.	0.0	0
52	Observation of threading dislocations with a c+m type Burgers vector in HVPE GaN substrates using multi-photon excitation photoluminescence and TEM. <i>Journal of Crystal Growth</i> , 2022, , 126748.	0.7	0